

# 2N7002PS

# 60 V, 320 mA N-channel Trench MOSFET Rev. 1 — 1 July 2010

Product data sheet

## **Product profile**

#### 1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- AEC-Q101 qualified

#### 1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
$V_{DS}$	drain-source voltage	T <sub>amb</sub> = 25 °C	-	-	60	V
$V_{GS}$	gate-source voltage	T <sub>amb</sub> = 25 °C	-	-	±20	V
I <sub>D</sub>	drain current	$T_{amb}$ = 25 °C; $V_{GS}$ = 10 V	[1] _	-	320	mA
R <sub>DSon</sub>	drain-source on-state resistance	$T_j = 25 ^{\circ}\text{C};$ $V_{GS} = 10 \text{V};$ $I_D = 500 \text{mA}$	-	1	1.6	Ω

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



#### 60 V, 320 mA N-channel Trench MOSFET

## 2. Pinning information

Table 2. Pinning

Table 2.	Pinning			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		
2	G1	gate1	6 5 4	D <sub>1</sub> D <sub>2</sub>
3	D2	drain2		
4	S2	source2	0	
5	G2	gate2	<u> </u>	
6	D1	drain1		$S_1$ $G_1$ $S_2$ $G_2$
				msd901

## 3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
2N7002PS	SC-88	plastic surface-mounted package; 6 leads	SOT363	

## 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
2N7002PS	M8*

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

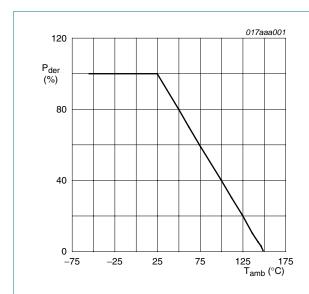
Symbol	Parameter	Conditions	Min	Max	Unit
Per trans	istor				
$V_{DS}$	drain-source voltage	T <sub>amb</sub> = 25 °C	-	60	V
$V_{GS}$	gate-source voltage	T <sub>amb</sub> = 25 °C	-	±20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V	<u>[1]</u>		
		T <sub>amb</sub> = 25 °C	-	320	mA
		T <sub>amb</sub> = 100 °C	-	240	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$	-	1.2	Α

#### 60 V, 320 mA N-channel Trench MOSFET

**Table 5.** Limiting values ...continued
In accordance with the Absolute Maximum Rating System (IEC 60134).

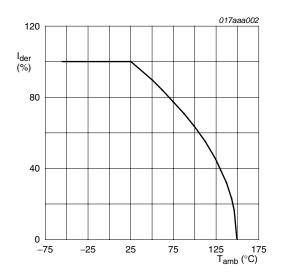
Symbol	Parameter	Conditions	Min	Max	Unit
P <sub>tot</sub>	total power dissipation	$T_{amb} = 25  ^{\circ}C$	[2] -	280	mW
			[1] -	320	mW
		$T_{sp} = 25  ^{\circ}C$	-	990	mW
Source-d	rain diode				
Is	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u> _	320	mA
Per device	e				
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2] -	420	mW
Tj	junction temperature			150	°C
T <sub>amb</sub>	ambient temperature		<b>–55</b>	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$ 

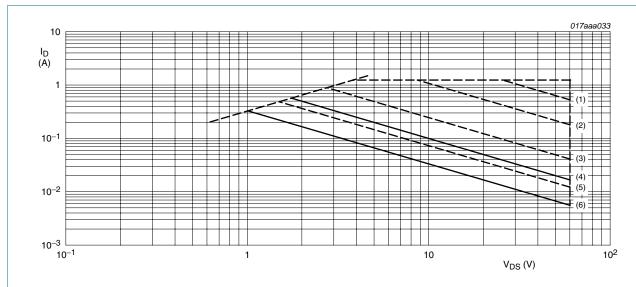
Fig 1. Normalized total power dissipation as a function of ambient temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

Fig 2. Normalized continuous drain current as a function of ambient temperature

#### 60 V, 320 mA N-channel Trench MOSFET



I<sub>DM</sub> = single pulse

- (1)  $t_p = 100 \mu s$
- (2)  $t_p = 1 \text{ ms}$
- (3)  $t_p = 10 \text{ ms}$
- (4) DC;  $T_{sp} = 25 \, ^{\circ}C$
- (5)  $t_p = 100 \text{ ms}$
- (6) DC;  $T_{amb} = 25 \, ^{\circ}C$ ; drain mounting pad 1 cm<sup>2</sup>

Fig 3. Per transistor: Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

#### 6. Thermal characteristics

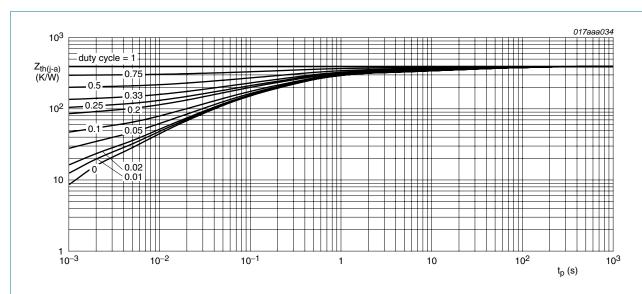
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
R <sub>th(j-a)</sub> thermal resistance from junction to ambient		in free air	<u>[1]</u> -	390	445	K/W
		[2] _	340	390	K/W	
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	130	K/W
Per device	)					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	300	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

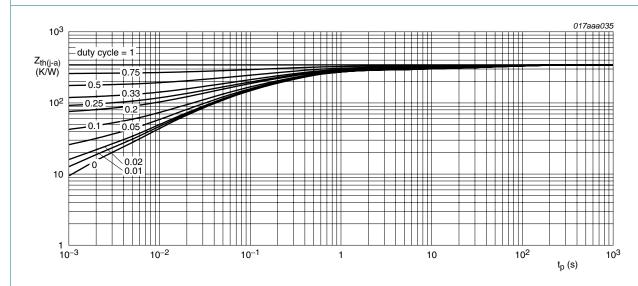
<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

#### 60 V, 320 mA N-channel Trench MOSFET



FR4 PCB, standard footprint

Fig 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

Fig 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 60 V, 320 mA N-channel Trench MOSFET

## 7. Characteristics

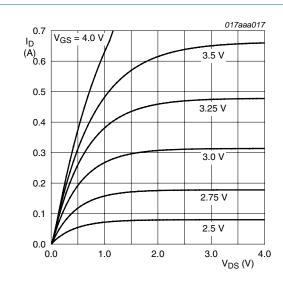
Table 7. Characteristics

 $T_i = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10 \mu A; V_{GS} = 0 V$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}$	1.1	1.75	2.4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$				
		T <sub>j</sub> = 25 °C	-	-	1	μΑ
		T <sub>j</sub> = 150 °C	-	-	10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	100	nΑ
R <sub>DSon</sub>	drain-source on-state resistance		<u>[1]</u>			
		$V_{GS} = 5 \text{ V}; I_D = 50 \text{ mA}$	-	1.3	2	Ω
		$V_{GS} = 10 \text{ V}; I_D = 500 \text{ mA}$	-	1	1.6	Ω
gfs g	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}$	<u>[1]</u> _	400	-	mS
Dynamic c	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 300 \text{ mA};$	-	0.6	8.0	nC
Q <sub>GS</sub>	gate-source charge	V <sub>DS</sub> = 30 V; - V <sub>GS</sub> = 4.5 V	-	0.2	-	nC
$Q_{GD}$	gate-drain charge	V <sub>GS</sub> = 4.5 V	-	0.2	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 10 \text{ V};$	-	30	50	pF
C <sub>oss</sub>	output capacitance	f = 1 MHz	-	7	-	pF
$C_{rss}$	reverse transfer capacitance		-	4	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DD</sub> = 50 V;	-	3	6	ns
t <sub>r</sub>	rise time	$R_L = 250 \Omega;$	-	4	-	ns
t <sub>d(off)</sub>	turn-off delay time	$V_{GS} = 10 \text{ V};$ $R_G = 6 \Omega$	-	10	20	ns
t <sub>f</sub>	fall time		-	5	-	ns
Source-dra	ain diode					
$V_{SD}$	source-drain voltage	$I_S = 115 \text{ mA}; V_{GS} = 0 \text{ V}$	0.47	0.75	1.1	V

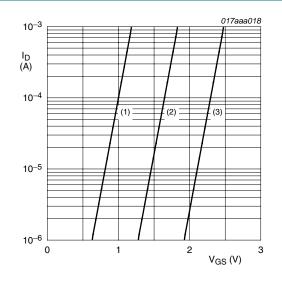
<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.01.$ 

#### 60 V, 320 mA N-channel Trench MOSFET



 $T_{amb} = 25 \, ^{\circ}C$ 

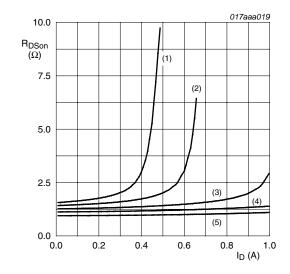
Fig 6. Per transistor: Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_{amb} = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$ 

- (1) minimum values
- (2) typical values
- (3) maximum values

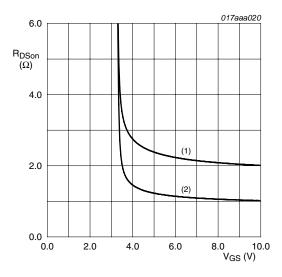
Fig 7. Per transistor: Sub-threshold drain current as a function of gate-source voltage



T<sub>amb</sub> = 25 °C

- (1)  $V_{GS} = 3.25 \text{ V}$
- (2)  $V_{GS} = 3.5 \text{ V}$
- (3)  $V_{GS} = 4 V$
- (4)  $V_{GS} = 5 V$
- (5)  $V_{GS} = 10 \text{ V}$

Fig 8. Per transistor: Drain-source on-state resistance as a function of drain current; typical values



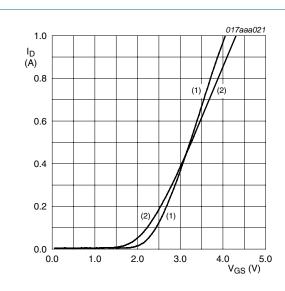
 $I_D = 500 \text{ mA}$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$

Fig 9. Per transistor: Drain-source on-state resistance as a function of gate-source voltage; typical values

2N7002PS

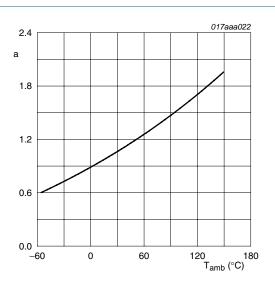
60 V, 320 mA N-channel Trench MOSFET



$$V_{DS} > I_{D} \times R_{DSon}$$

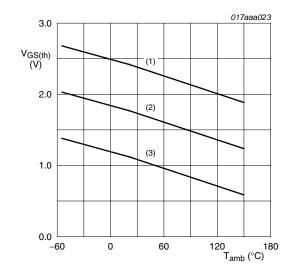
- (1)  $T_{amb} = 25 \, ^{\circ}C$
- (2)  $T_{amb} = 150 \, ^{\circ}C$

Fig 10. Per transistor: Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

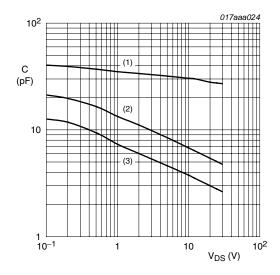
Fig 11. Per transistor: Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Per transistor: Gate-source threshold voltage as a function of ambient temperature

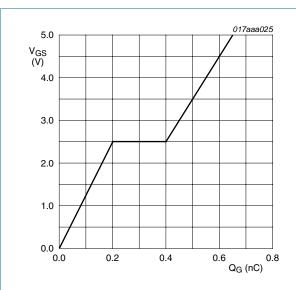


f = 1 MHz; V<sub>GS</sub> = 0 V

- (1) C<sub>iss</sub>
- (2) Coss
- (3)  $C_{rss}$

Fig 13. Per transistor: Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 60 V, 320 mA N-channel Trench MOSFET



 $I_D = 300 \text{ mA}$ ;  $V_{DS} = 30 \text{ V}$ ;  $T_{amb} = 25 ^{\circ}\text{C}$ 

Fig 14. Per transistor: Gate-source voltage as a function of gate charge; typical values

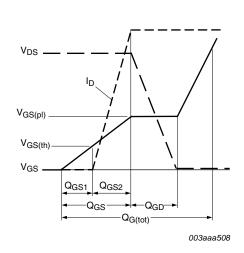
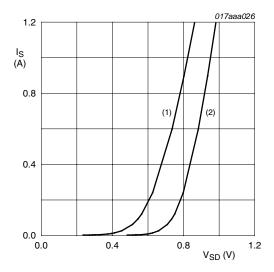


Fig 15. Per transistor: Gate charge waveform definitions



 $V_{GS} = 0 V$ 

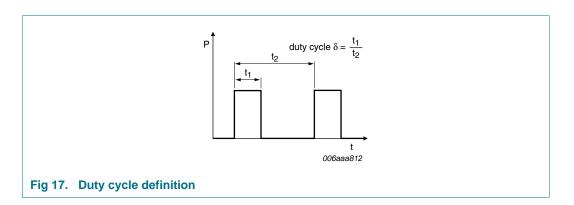
(1)  $T_{amb} = 150 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

Fig 16. Per transistor: Source current as a function of source-drain voltage; typical values

60 V, 320 mA N-channel Trench MOSFET

## 8. Test information



## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

#### 60 V, 320 mA N-channel Trench MOSFET

## 9. Package outline

#### Plastic surface-mounted package; 6 leads

**SOT363** 

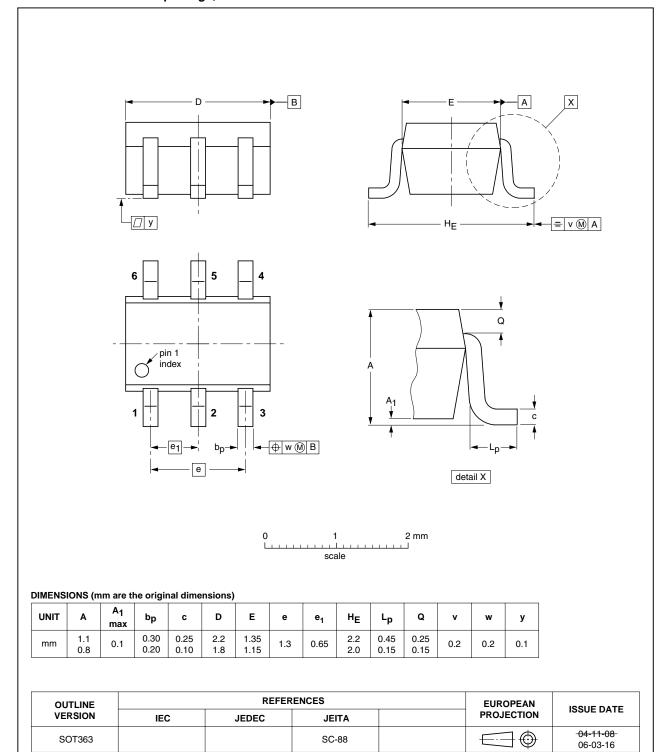


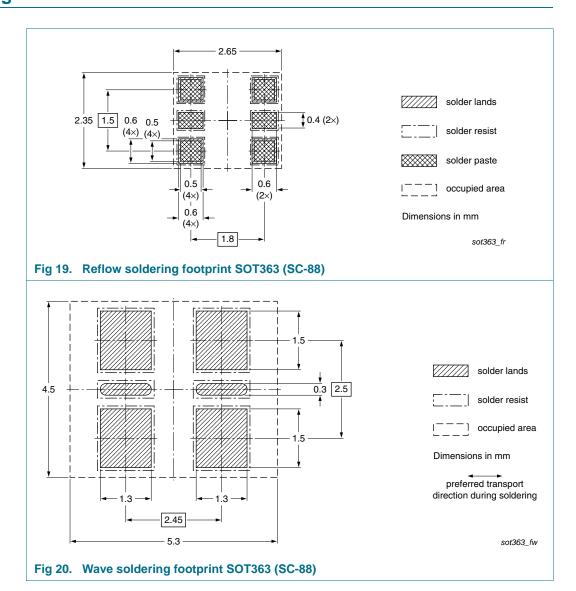
Fig 18. Package outline SOT363 (SC-88)

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#### 60 V, 320 mA N-channel Trench MOSFET

## 10. Soldering



#### 60 V, 320 mA N-channel Trench MOSFET

## 11. Revision history

#### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
2N7002PS v.1	20100701	Product data sheet	-	-

#### 60 V, 320 mA N-channel Trench MOSFET

### 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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#### 60 V, 320 mA N-channel Trench MOSFET

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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#### 60 V, 320 mA N-channel Trench MOSFET

#### 14. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information
4	Marking 2
5	Limiting values
6	Thermal characteristics 4
7	Characteristics 6
8	Test information 10
8.1	Quality information
9	Package outline
10	Soldering 12
11	Revision history 13
12	Legal information 14
12.1	Data sheet status
12.2	Definitions
12.3	Disclaimers
12.4	Trademarks 15
13	Contact information
14	Contents

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